

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1	10/759609	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:21
L3	4	"4233615".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:43
L4	2	"20050098807"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:48
L5	653205	nm nanometer nano adj meter angstrom ang ".ang."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:48
L6	2329593	thick\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:48
L7	1	4 and 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:50
L8	4	"6252796".pn. "6785100".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:50
L9	1	8 and 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 14:50
L10	595313	resistive adj2 (element device film layer) resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:25
L11	1919840	voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:25

L12	266516	high adj 11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:26
L13	153722	low adj 11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:28
L14	2940306	insulat\$4 dielectric oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:29
L15	4164265	thin light\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:33
L16	1580286	thick heav\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:30
L17	307151	(high adj voltage) (thick heav\$4) near2 (insulat\$4 dielectric oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:34
L18	263740	(low adj voltage) (thin light\$4) near2 (insulat\$4 dielectric oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:58
L19	827460	(transistor tft) (fet mosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:35
L20	12473	17 near2 19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:36
L21	10295	18 near2 19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:36

L22	1804	20 with 21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:36
L23	85	22 with 10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:55
L24	1355	20.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:36
L25	1283	21.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:37
L26	87939	10.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:37
L27	77	24 and 25 and 26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:37
L28	22	24 and 25 and 26	US-PGPUB	OR	ON	2005/09/16 15:37
L29	5302226	pattern\$4 etch\$4 remov\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:55
L30	257107	29 near3 14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:57
L31	2460	30 with 10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:58
L32	74	31 with 18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:58

L33	1	31 with 21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:59
L34	1	32 and 27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:59